SENSITRON
SEMICONDUCTOR

TECHNICAL DATA
DATA SHEET 930, REV. C

ULTRA FAST RECOVERY SILICON RECTIFIER DIE

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage DC Blocking Voltage Breakdown Voltage	V_{RWM} V_R V_{BR}	-	150	V
Max. Average Forward Current	$I_{F(AV)}$	@ 55°C	1.0	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, sine pulse (1)	35	A
Die Size	-	-	40	mil
Max. Junction Temperature	T_J	-	-55 to +175	°C
Max. Storage Temperature	T_{stg}	-	-55 to +175	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	1A, pulse, T_J = 25 °C	0.875	V
	V_{F2}	2.5A, pulse, T_J = 25 °C	0.975	V
	V_{F3}	1A, pulse, T_J = 100 °C	0.800	V
Max. Reverse Current	I_{R1}	$V_R = V_{RWM}$, pulse, T_J = 25 °C	1.0	µA
	I_{R2}	$V_R = V_{RWM}$, pulse, T_J = 100 °C	50	µA
Reverse Recovery Time	t_{rr}	$I_F = I_R$ = 0.5A , I_{RM} = 0.05A	25	ns
Max. Junction Capacitance	C_T	V_R = 10V, T_C = 25 °C f_{SIG} = 1MHz, V_{SIG} = 50mV (p-p)	25	pF

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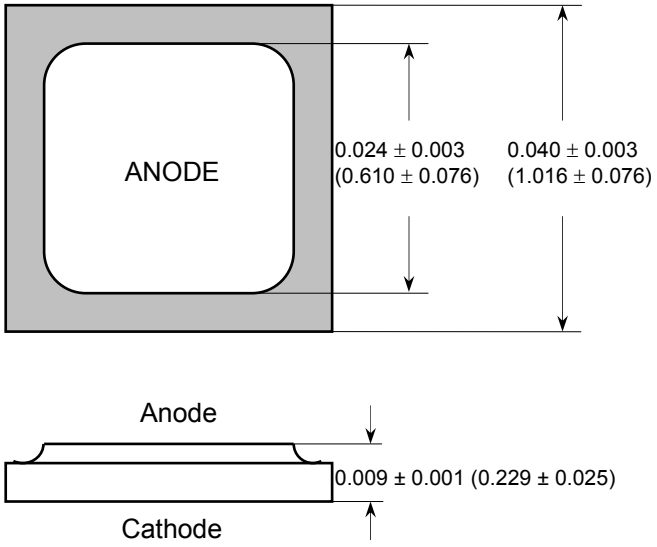
Mechanical Dimensions: In Inches (mm)



Bottom side metalization: Ti/Ni/Ag - 30 kÅ minimum.

Top side metalization: Al - 25 kÅ minimum

Bottom side is cathode, top side is anode.